

28th International Symposium on Superconductivity, ISS 2015, November 16-18, 2015, Tokyo, Japan

Change of the surface structure by F doping in BiS₂-based superconductor CeO_{1-x}F_xBiS₂

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Abstract

The observation of the surface structure on single crystalline CeO_{1-x}F_xBiS₂ ($x = 0.5$, and 0.7) was performed successfully using a scanning tunneling microscopy. In the sample with $x = 0.5$, the square lattice composed of Bi atoms was observed. In addition, defects of the surface atoms and streaks were detected on the surface as in the case of NdO_{0.7}F_{0.3}BiS₂ single crystal. With further F doping, the surface structure of sample with $x = 0.7$ showed a novel structure, termed by the "bone" structure. This result suggests that the F concentration affects the surface structure.

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Peer-review under responsibility of the ISS 2015 Program Committee

Keywords: Superconductivity; BiS₂-superconductor; Scanning tunneling microscopy (STM)

1. Introduction

It is well known that the superconductors with the layered structure such as cuprates and iron-based superconductors show the high temperature superconductivity and the novel electronic structure. Thus, the layered superconductors are paid much attention in the condensed matter physics. Newly discovered BiS₂-based superconductors have a layered structure composed of the conductive BiS₂ layers and non-conductive block layers [1-15]. Up to now, 13 materials which have different block layers have been found in the BiS₂-based family. Among them, LnOBiS₂ ($Ln = La, Pr, Ce, Nd, Sm, Yb$, and Bi) show superconductivity by the substitution of F⁻ ions for O²⁻

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ions. The substitution of F⁻ ion induces not only carrier doping but also the structural change. It has been pointed out that the superconducting transition temperatures of these materials are sensitive to the crystal structure [16,17]. Furthermore, these materials have been pointed out that there is instability against the formation of charge density wave [18-20]. Thus, the measurements which clarify the structure are crucial in the study of these materials. In fact, the novel electronic structure, so-called “checkerboard stripe” structure, has been observed on the surface of the single crystalline NdO_{0.7}F_{0.3}BiS₂ using scanning microscopy (STM) and spectroscopy (STS) measurement [21].

Here, we report on the F concentration dependence of the surface structure of BiS₂-based superconductor CeO_{1-x}F_xBiS₂ ($x = 0.5$, and 0.7) by STM. Square lattice consisted of Bi atoms was observed successfully on the surface of single crystalline CeO_{0.5}F_{0.5}BiS₂. Furthermore, an additional structure was observed on the surface of the CeO_{0.3}F_{0.7}BiS₂ single crystal.

2. Experimental

Single crystalline samples of CeO_{1-x}F_xBiS₂ ($x = 0.5$, and 0.7) were synthesized by a CsCl/KCl flux method in evacuated quartz tubes [22,23]. Mixtures of Bi, Bi₂S₃, Bi₂O₃, BiF₃, and Ce₂S₃ were ground with nominal compositions of CeO_{1-x}F_xBiS₂ ($x = 0.5$, and 0.7). Bi₂S₃ was obtained by sintering the mixtures of Bi and S in the evacuated quartz tube at 500 °C for 10 hours. The mixture of 0.8 g was mixed with CsCl/KCl powder of 5 g, and sealed in an evacuated quartz tube. The tube was heated at 800 °C for 10 hours and cooled down to 600 °C. After this thermal process, the sintered materials were washed by distilled water to remove the flux. Scanning tunneling microscopy (STM) measurements were performed at 4 K in the He gas using a laboratory-build scanning tunneling microscope. A surface of single crystals was prepared by cleaving the sample at 4K in situ. A bias voltage was applied to the sample in all measurements.

3. Results

Figure 1 shows the STM image of the surface structure on the single crystalline CeO_{0.5}F_{0.5}BiS₂. The square lattice with a period of approximately 4 Å can be seen in the surface structure (see Fig. 1(b)). This period is corresponding to the lattice parameter a of CeO_{0.5}F_{0.5}BiS₂ [4,24]. Because the cleavage occurs between two BiS₂ layers which bond weakly through Van der Waals force, the exposed surface is BiS₂ layer. The observed atoms are considered to be Bi ions as was reported in NdO_{0.7}F_{0.3}BiS₂ single crystal [21,25]. In addition to the periodic lattice, there are several defects of the Bi ions. The ratio of the defects is approximately 2% in the observed area shown in Fig. 1(a). Near the defects, there exist the streaks along the each diagonal direction of the square lattice, as shown in white arrows in the Fig. 1(b). These defects and streaks are also reported in NdO_{0.7}F_{0.3}BiS₂, though the ratio of the defects is slightly larger in NdO_{0.7}F_{0.3}BiS₂. Thus, the replacement of the block layer from NdO_{0.7}F_{0.3} to CeO_{0.5}F_{0.5} does not change the surface structure of the BiS₂ layer a lot.

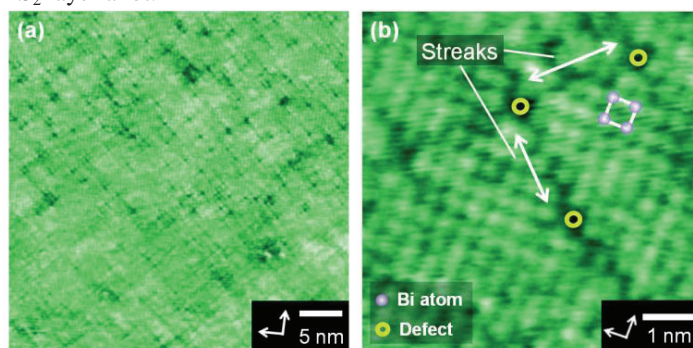


Fig. 1 (Color online)

(a) STM image at the bias voltage of 500 mV on the surface for single crystal of CeO_{0.5}F_{0.5}BiS₂. (b) STM image of another area in CeO_{0.5}F_{0.5}BiS₂ at the bias voltage of 800 mV. The filled circles formed the square are Bi atoms. The unfilled circles and white arrows show defects, and streaks, respectively.

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